



## Die Related Grand Summary Data

Activation Energy	0.7	electron-volts
Die Junction Temperature	55	Celsius
One-sided Upper Confidence Level	90	percent

BUCKET	REJ	EDH	TEST DEV	FIT
ACMOS	0	282,269,282	MAX809STR	8.2
BICMOS	0	100,161,976	MC100EPT23D	23.0
BP STD LINEAR	1	1,691,310,665	LM317T	2.3
BPT	0	1,056,009,285	MJ10012	2.2
CMOS STD	0	1,024,306,361	MCW14001B	2.2
CMOS SUB	0	876,508,783	MC74LCX14D	2.6
MOSAIC1/1.5	0	164,121,502	SC64017L	14.0
MOSAIC3	4	1,012,742,604	SCW63800	7.9
MOSAIC5	0	997,263,815	NBSX1125D	2.3
PWR SENSE	7	1,064,996,705	NCP5355D	14.5
RECT	40	4,805,989,086	MR2502	10.3
SiGe	0	236,394,610	NBDSG11	9.7
SSD	0	384,087,657	MSD6150	6.0
SST	0	949,095,848	2N4123	2.4
THYRISTOR	1	685,345,982	2N6075	5.7
TMOS HD	3	3,560,940,180	JDX5014	1.9
TMOS IGBT	0	183,102,874	MGP20N60	12.6
TMOS STD	2	3,491,749,121	2N7008	1.5
TMOS Trench	3	564,460,956	NTD4804N-1G	11.8
VHVIC	7	521,307,172	MC33362P	22.6
ZENER	0	1,661,427,872	1.5KE11A	1.4